

SC040N120H7-R

Silicon Carbide MOSFET 1200V, 30mΩ, 60A



重庆平伟半导体股份有限公司

Features

- 1200V turn-off gate voltage can be applied
- High Blocking Voltage with Low RDS(on)
- High Speed Switching with Low Capacitances
- Easy to Parallel and Simple to Drive
- Qualified according to JEDEC criteria

Applications

- Lighting
- Telecom and UPS
- PWM stages for e.g. PC Silverbox, Adapter, LCD & PDP TV



100% DVDS Tested

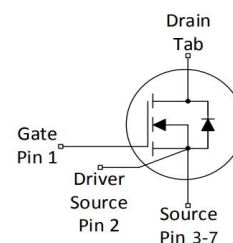
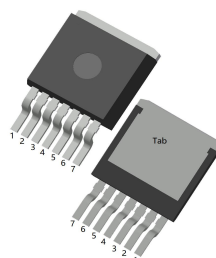
100%

Avalanche Tested

Product Summary

V_{DS}	1200V
$R_{DS(on)}$ typ.	30mΩ
I_D	60A

TO-263-7H



Package Marking and Ordering Information

Part #	Marking	Package	Packing	Reel Size	Tape Width	Qty
SC040N120H7-R	SC040N120H7-R	TO-263-7H	Tube	N/A	N/A	30pcs

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	1200	V
Continuous drain current $T_C = 25^\circ\text{C}$ $T_C = 100^\circ\text{C}$	I_D	60 42	A
Pulsed drain current ($T_C = 25^\circ\text{C}$)	$I_{D \text{ pulse}}$	180	A
Avalanche energy, single pulse ($L=5\text{mH}$)	E_{AS}	331	mJ
Gate-Source voltage,max.transient voltage	V_{GSmax}	-8/+22	V
Recommended operating values	V_{GSsop}	0/+15 to 18	V
Power dissipation $T_C = 25^\circ\text{C}$	P_{tot}	208	W
Operating junction and storage temperature	T_j, T_{stg}	-55...+175	$^\circ\text{C}$

Thermal Resistance

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Thermal resistance, junction – case.	R_{thJC}	-	0.48	0.7	°C/W	-
Thermal resistance, junction - ambient(min. footprint)	R_{thJA}	-	-	50.0	°C/W	

Electrical Characteristic (at $T_j = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		

Static Characteristic

Drain-source breakdown voltage	BV_{DSS}	1200	-	-	V	$V_{GS}=0V, I_D=100\mu A$
Gate threshold voltage	$V_{GS(th)}$	1.5	2.7	4.0	V	$V_{DS}=V_{GS}, I_D=10mA$
Zero gate voltage drain current	I_{DSS}	-	1	10	μA	$V_{DS}=1200V, V_{GS}=0V$ $T_j=25^{\circ}\text{C}$
Gate-source leakage current	I_{GSS}	-	-	200	nA	$V_{GS}=20V, V_{DS}=0V$
		-	-	-200	nA	$V_{GS}=-5V, V_{DS}=0V$
Drain-source on-state resistance	$R_{DS(on)}$	-	30	40	mΩ	$V_{GS}=18V, I_D=30A, T_j=25^{\circ}\text{C}$
Drain-source on-state resistance	$R_{DS(on)}$	-	63	-	mΩ	$V_{GS}=18V, I_D=30A, T_j=175^{\circ}\text{C}$
Transconductance	g_{fs}	-	20.0	-	S	$V_{DS}=20V, I_D=20A$

Dynamic Characteristic

Input Capacitance	C_{iss}	-	2959	-	pF	$V_{GS}=0V, V_{DS}=1000V,$ $f=1MHz$
Output Capacitance	C_{oss}	-	118	-		
Reverse Transfer Capacitance	C_{rss}	-	6	-		
Gate Total Charge	Q_G	-	117	-	nC	$V_{DS}=800V, I_D=33A$ $, V_{GS}=-5/18V$
Gate-Source charge	Q_{gs}	-	38	-		
Gate-Drain charge	Q_{gd}	-	32	-		
Turn-on delay time	$t_{d(on)}$	-	44	-	ns	$V_{GS}=-5/18V, V_{DD}=800V,$ $R_G=5\Omega, I_D=33A$
Rise time	t_r	-	15	-		
Turn-off delay time	$t_{d(off)}$	-	37	-		
Fall time	t_f	-	14	-		
Gate resistance	R_G	-	2.8	-	Ω	$V_{GS}=0V, f=1MHz$

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Body Diode Characteristic

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Body Diode Forward Voltage	V_{SD}	-	3.5	-	V	$V_{GS} = -5V, I_{SD} = 20A$ $T_j = 25^{\circ}C$
		-	3.2	-		$T_j = 175^{\circ}C$
Body Diode Continuous Forward Current	I_S	-	60		A	$T_C = 25^{\circ}C$
		-	42		A	$T_C = 100^{\circ}C$
Body Diode Reverse Recovery Time	t_{rr}	-	32	-	ns	$V_{GS} = 15V, I_{SD} = 33A,$ $V_R = 800V$ $di/dt = 1200A/us$
Body Diode Reverse Recovery Charge	Q_{rr}	-	226	-	nC	
Peak Reverse Recovery Current	I_{RRM}	-	10.4	-	A	

Typical Performance Characteristics

Fig 1: Output Characteristics $T_j=25^{\circ}\text{C}$

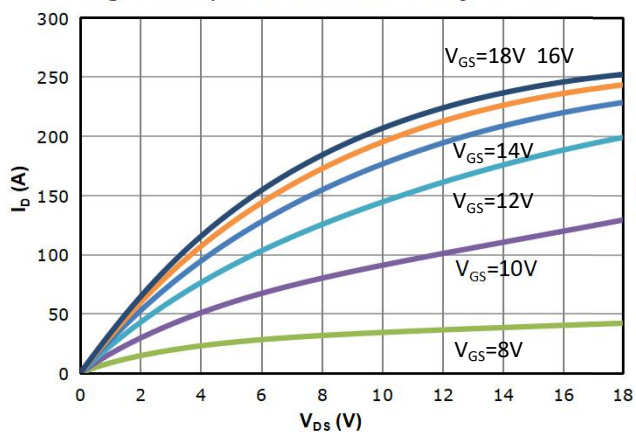


Fig 2: Output Characteristics $T_j=175^{\circ}\text{C}$

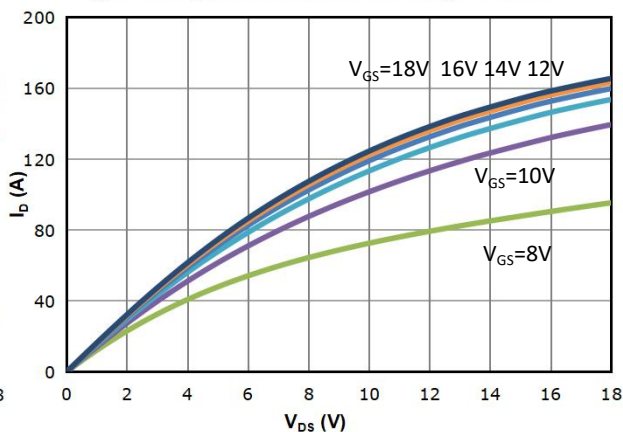


Fig 3: Transfer Characteristics

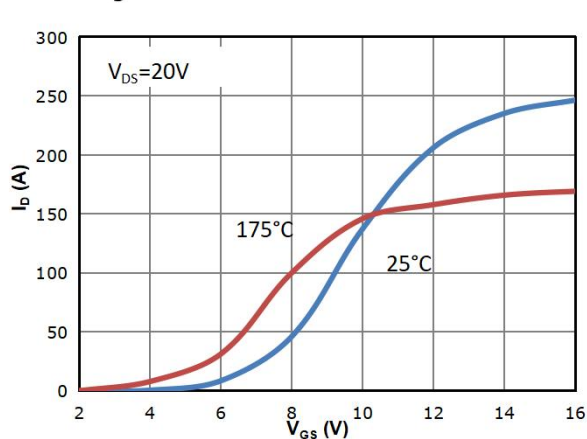


Fig 4: $R_{ds(on)}$ vs Drain Current and Gate Voltage

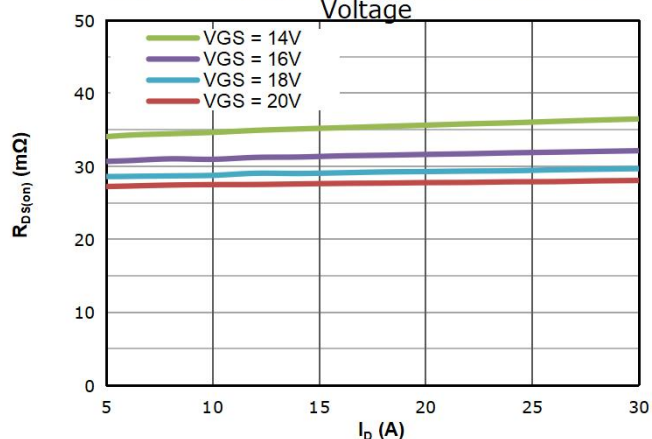


Fig 5: $R_{ds(on)}$ vs. Temperature

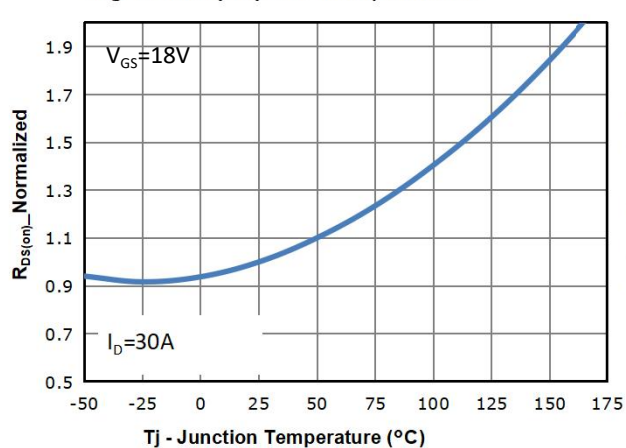


Fig 6: $V_{gs(th)}$ vs. Temperature

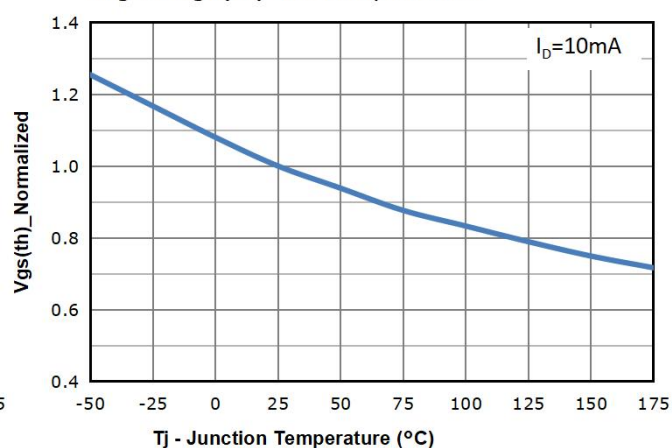


Fig 7: BVdss vs. Temperature

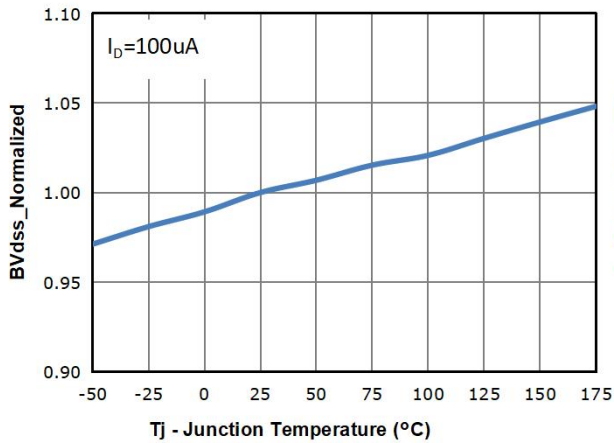


Fig 8: Capacitance Characteristics

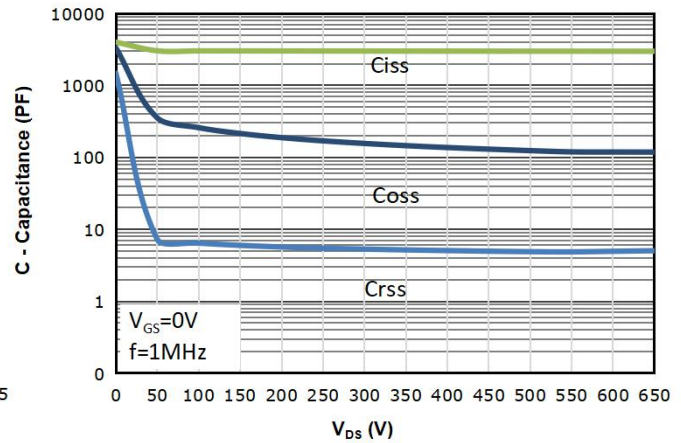


Fig 9: Gate Charge Characteristics

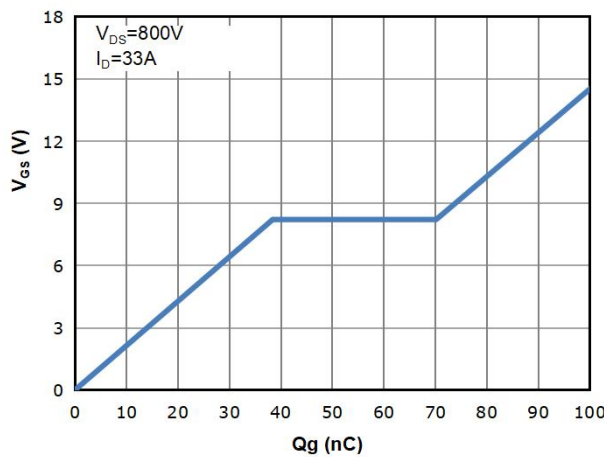


Fig 10: Body-diode Forward Characteristics

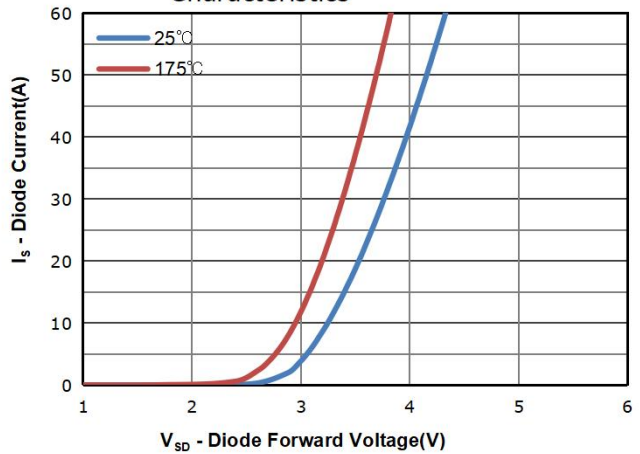


Fig 11: Power Dissipation

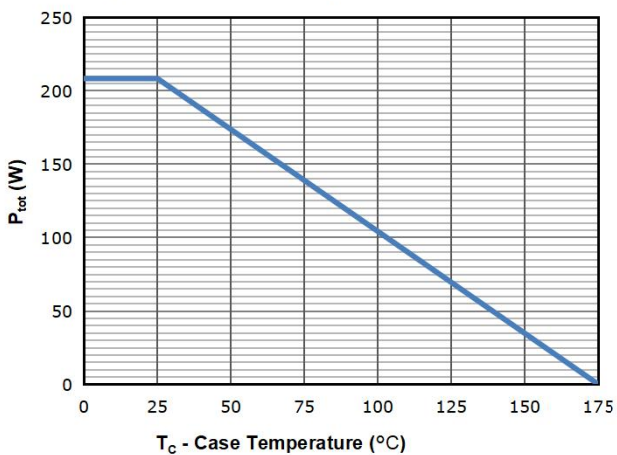


Fig 12: Drain Current Derating

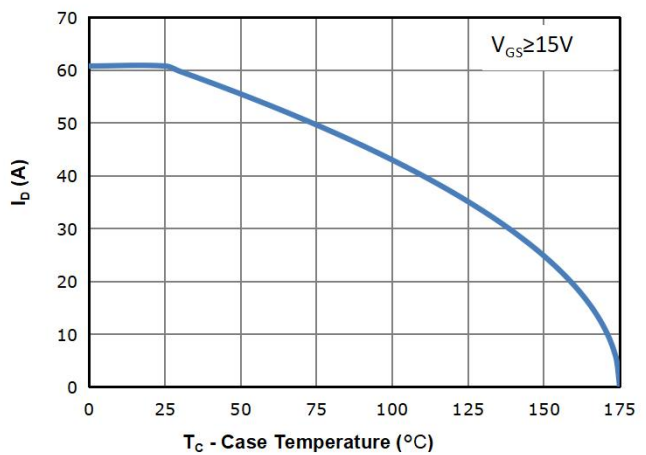


Fig 13: Safe Operating Area

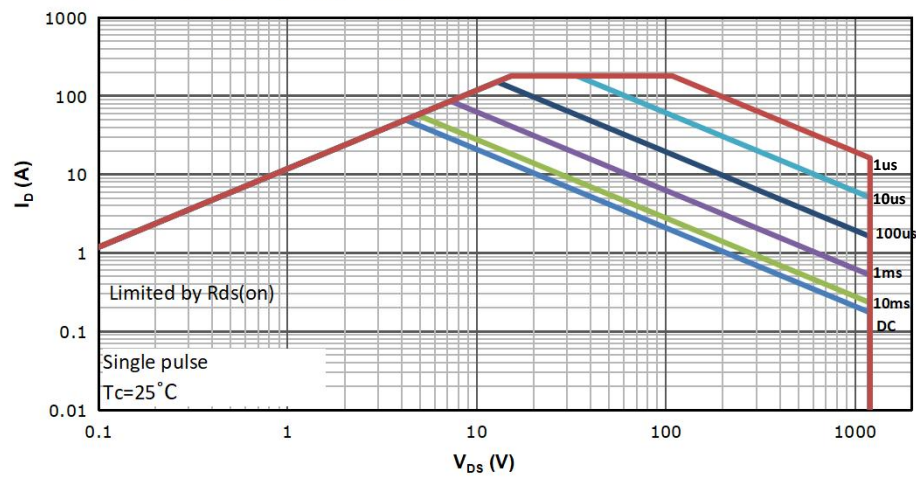
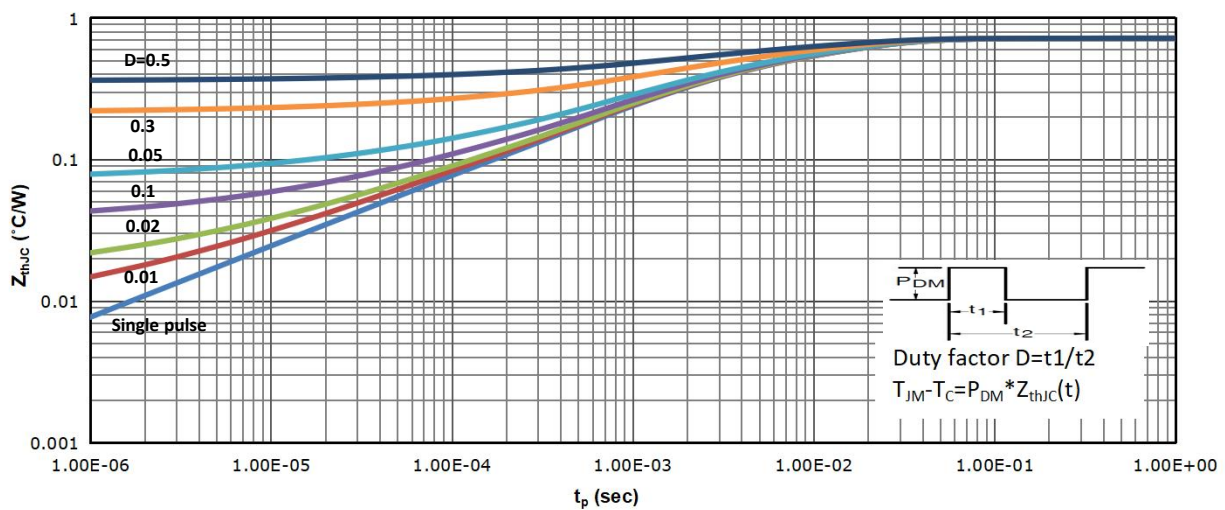
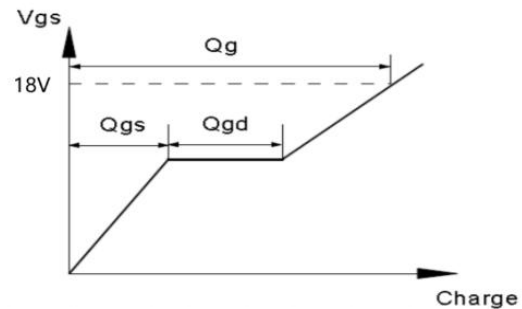
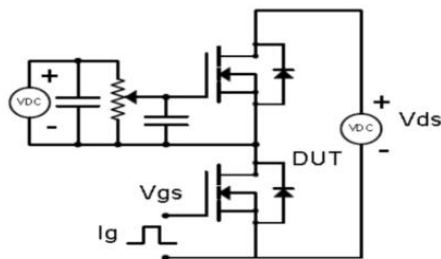


Fig 14: Max. Transient Thermal Impedance

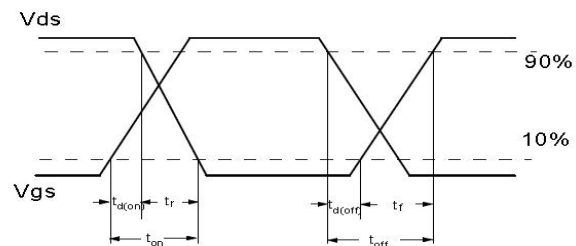
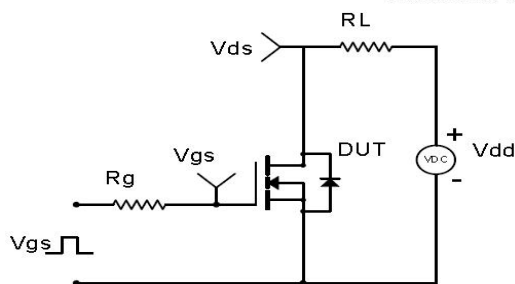


Test Circuit & Waveform

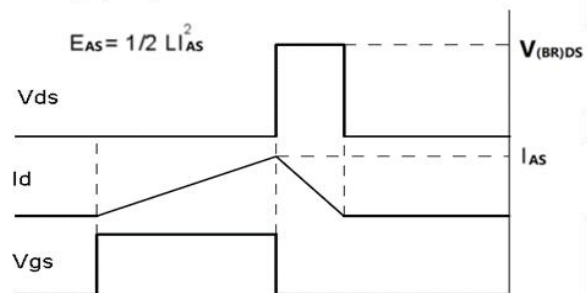
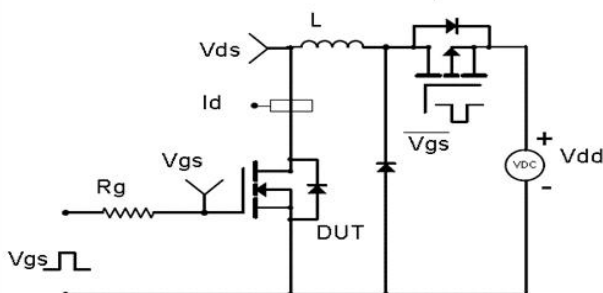
Gate Charge Test Circuit & Waveform



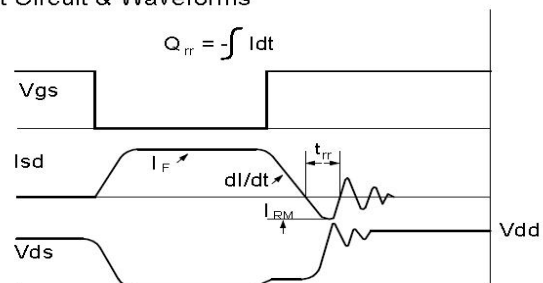
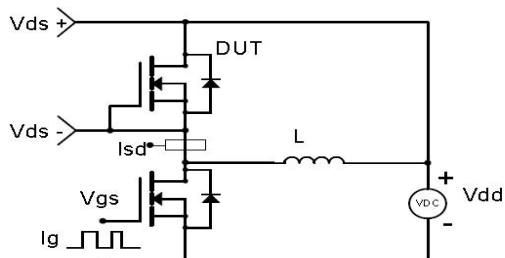
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



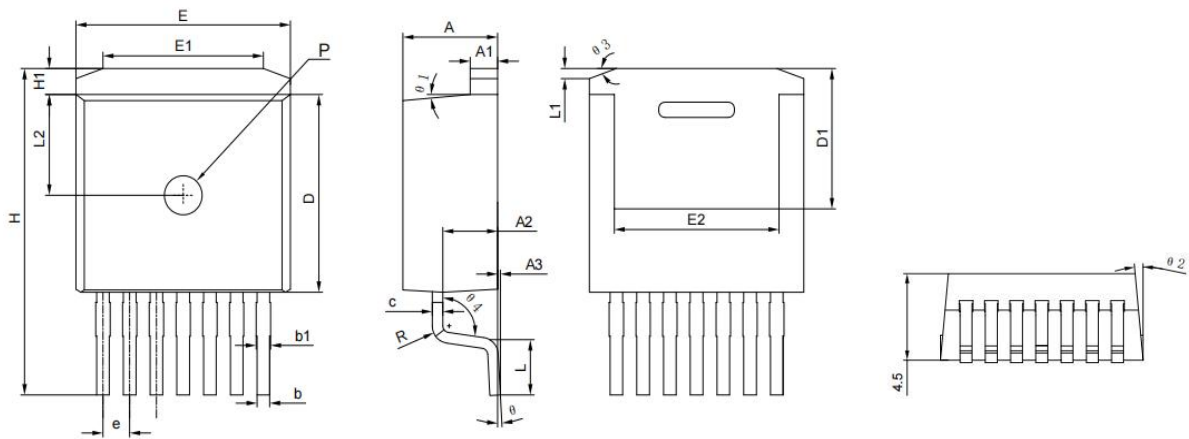
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Package Outline: TO-263-7H



SYMBOL	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.40	4.60	0.173	0.181
A1	1.25	1.40	0.049	0.055
A2	2.45	2.70	0.096	0.106
A3	0.05	0.20	0.002	0.008
b	0.50	0.70	0.020	0.028
b1	0.60	0.85	0.024	0.033
c	0.45	0.60	0.018	0.024
D	8.88	9.28	0.350	0.365
D1	5.80	6.40	0.228	0.252
E	9.18	10.28	0.361	0.405
E1	6.67	7.47	0.263	0.294
E2	6.90	7.60	0.272	0.299
e	1.27		0.050	
H	14.80	15.20	0.583	0.598
H1	1.10	1.30	0.043	0.051
L	2.35	2.75	0.093	0.108
L1	0.37	0.77	0.015	0.030
L2	4.48	4.78	0.176	0.188
θ	0°	5°	0°	5°
θ1	3°	7°	3°	7°
θ2	3°	7°	3°	7°
θ3	15°	25°	15°	25°
θ4	93°	100°	93°	100°
R	0.75	0.85	0.030	0.033
p	1.70	1.90	0.067	0.075

Disclaimer

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